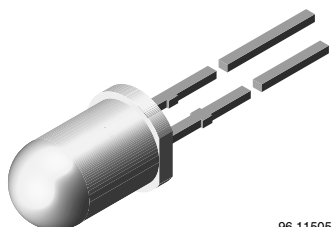


High Power Infrared Emitting Diode, RoHS Compliant, 940 nm, GaAlAs/GaAs



96 11505

DESCRIPTION

TSAL5300 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a blue-gray plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 940$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 22^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

- Infrared remote control units with high power requirements
- Free air transmission systems
- Infrared source for optical counters and card readers

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSAL5300	45	± 22	940	800

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSAL5300	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSAL5300-MSZ	Tape and ammpack	MOQ: 5000 pcs, 1000 pcs/ammopack	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu s$	I_{FSM}	1.5	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	$^\circ C$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ C$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R_{thJA}	230	K/W

Note

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified



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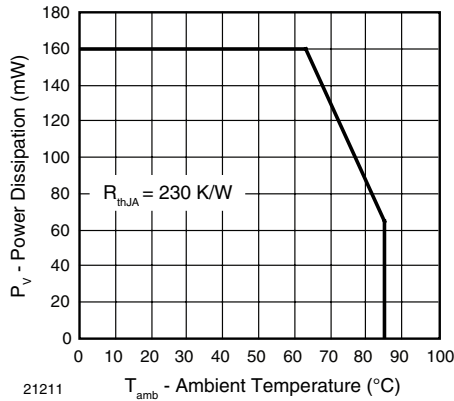


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

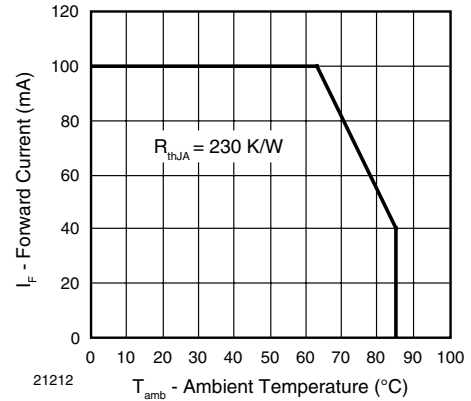


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F		1.35	1.6	V
	I _F = 1 A, t _p = 100 μs	V _F		2.6	3	V
Temperature coefficient of V _F	I _F = 1 mA	TKV _F		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _j		25		pF
Radiant intensity	I _F = 100 mA, t _p = 20 ms	I _e	30	45	150	mW/sr
	I _F = 1 A, t _p = 100 μs	I _e	260	350		mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	φ _e		35		mW
Temperature coefficient of φ _e	I _F = 20 mA	TKφ _e		- 0.6		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I _F = 100 mA	λ _p		940		nm
Spectral bandwidth	I _F = 100 mA	Δλ		50		nm
Temperature coefficient of λ _p	I _F = 100 mA	TKλ _p		0.2		nm/K
Rise time	I _F = 100 mA	t _r		800		ns
	I _F = 1 A	t _r		500		ns
Fall time	I _F = 100 mA	t _f		800		ns
	I _F = 1 A	t _f		500		ns
Virtual source diameter	Method: 63 % encircled energy	d		2.3		mm

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

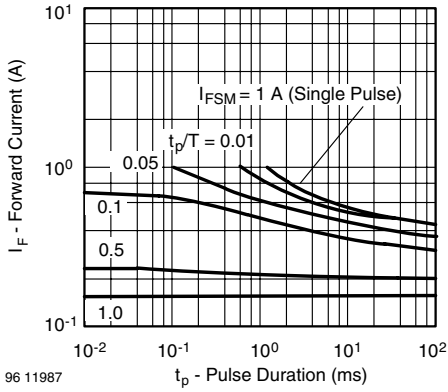


Fig. 3 - Pulse Forward Current vs. Pulse Duration

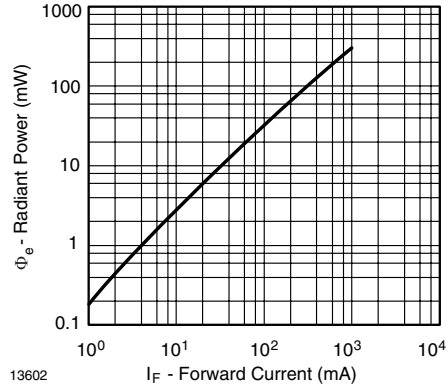


Fig. 6 - Radiant Power vs. Forward Current

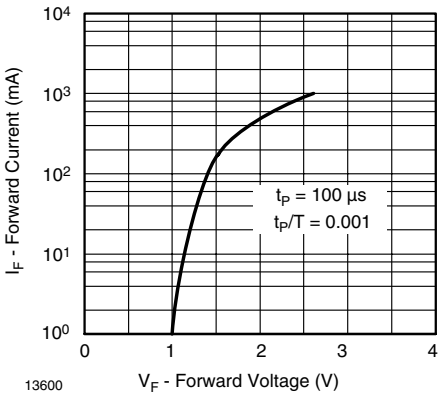


Fig. 4 - Forward Current vs. Forward Voltage

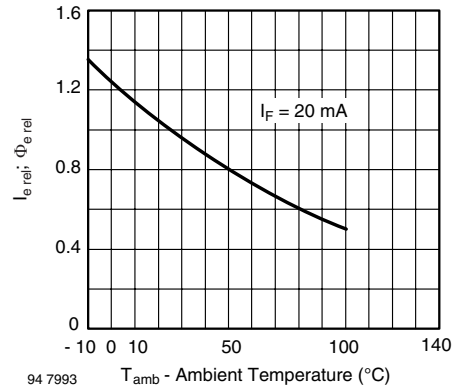


Fig. 7 - Relative Radiant Intensity/Power vs. Ambient Temperature

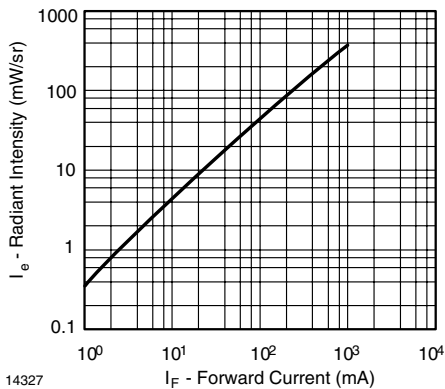


Fig. 5 - Radiant Intensity vs. Forward Current

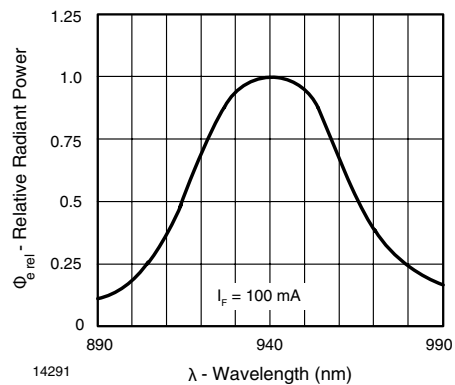


Fig. 8 - Relative Radiant Power vs. Wavelength

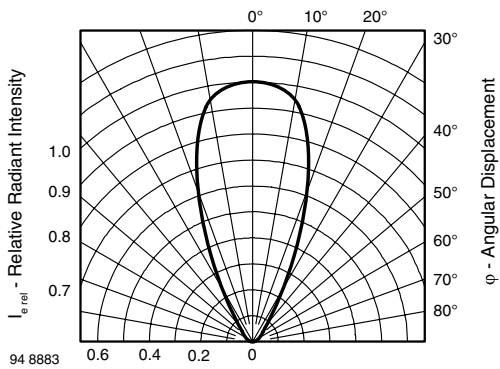
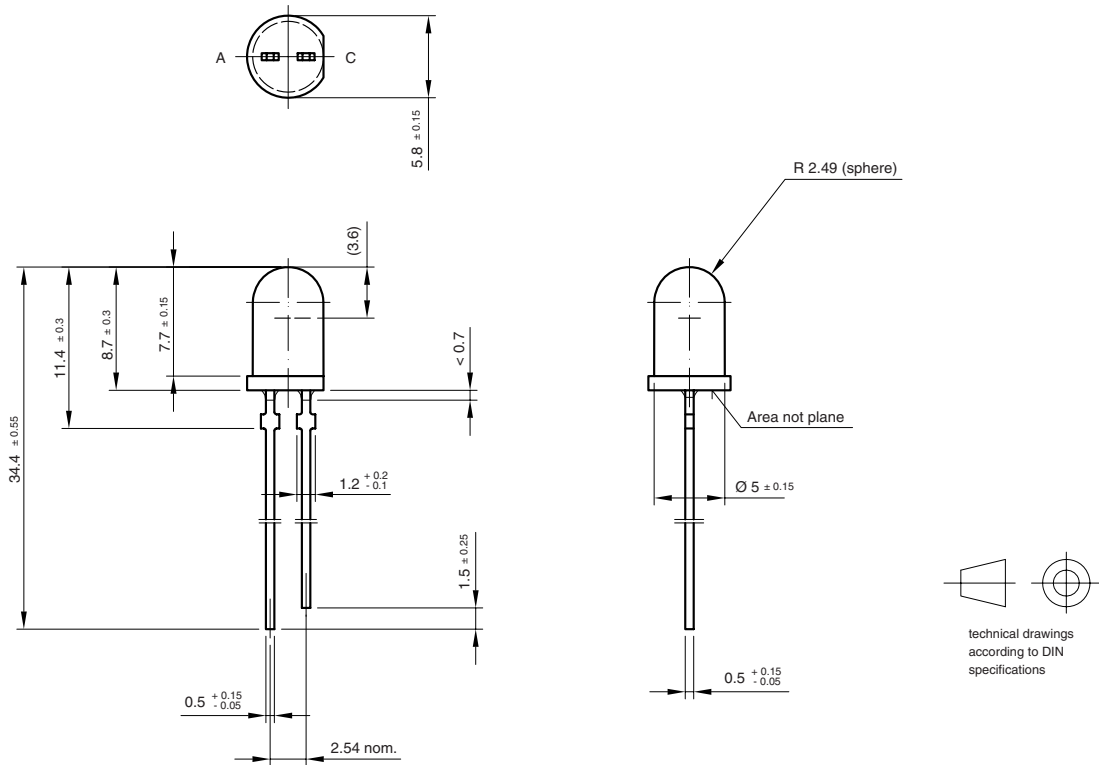


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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TSAL5300

Vishay Semiconductors

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TAPE DIMENSIONS TSAL5300		
OPTION	H ± 0.5 mm	QUANTITY/BOX
CS21Z	22	1000
FSZ	27	1000
GSZ	29	1000
MSZ	25.5	1000

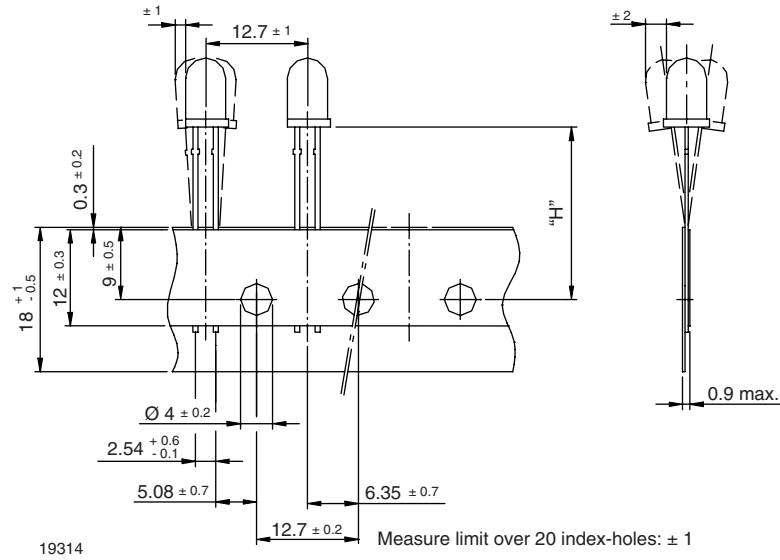


Fig. 10 - Ø 5 mm Devices on Tape

AMMOPACK

The tape is folded in a concertina arrangement and laid in cardboard box.

If components are required with cathode before the anode (figure 12), then start of tape should be taken from the side of the box marked “-”. If components are required with anode before cathode, then tape should be taken from the side of the box marked “+”.

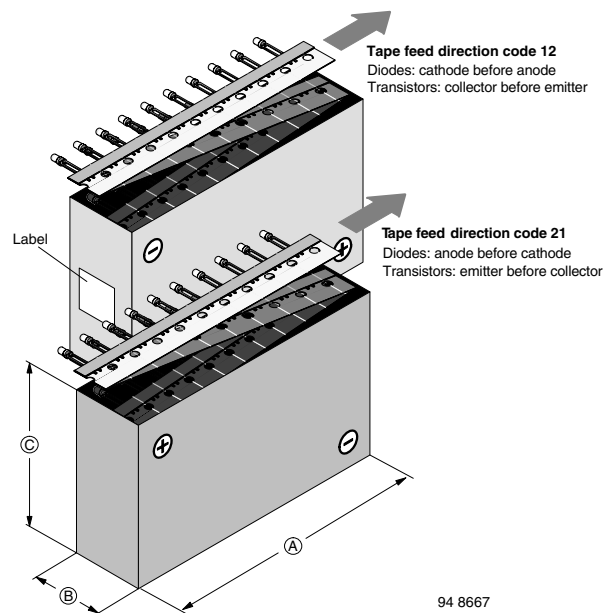


Fig. 11 - Tape Direction



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